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High-Power Diode Laser Technology and Applications X

Mark S. Zediker
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Introduction

This is the tenth year of the High-Power Diode Laser Technology and Applications Conference. When this conference started, the state of the art laser diode produced 50 watts with a 45-50% efficiency. Over the years, there was a steady increase in both the power and the efficiency of these devices and this year, 200-watt bars were the standard with >70% efficiency. This conference has played a pivotal role in this evolution, allowing the authors to share their results and compete with each other in a very open environment. This year, we also saw papers on breakthrough performance in laser diode system brightness and power. With laser diode systems matching the brightness of conventional lasers systems, the next ten years promise to be interesting, as these systems evolve and continue to achieve breakthrough efficiency and performance. I look forward to the next ten years because of the bright future for direct diode laser systems.

Mark S. Zediker